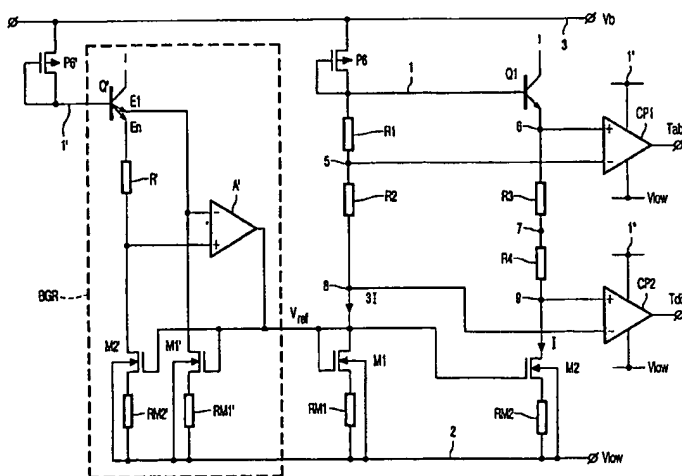




INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : H01L 27/02	A2	(11) International Publication Number: WO 98/37581 (43) International Publication Date: 27 August 1998 (27.08.98)
(21) International Application Number: PCT/IB98/00118 (22) International Filing Date: 29 January 1998 (29.01.98) (30) Priority Data: 9703453.2 19 February 1997 (19.02.97) GB 9717051.8 13 August 1997 (13.08.97) GB (71) Applicant: KONINKLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL). (71) Applicant (for SE only): PHILIPS NORDEN AB [SE/SE]; Kottbygatan 7, Kista, S-164 85 Stockholm (SE). (72) Inventor: KELLY, Brendan, Patrick; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). (74) Agent: STEVENS, Brian, T.; Internationaal Octrooibureau B.V., P.O. Box 220, NL-5600 AE Eindhoven (NL).		(81) Designated States: JP, KR, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>Without international search report and to be republished upon receipt of that report.</i>

(54) Title: POWER SEMICONDUCTOR DEVICES WITH A TEMPERATURE SENSOR CIRCUIT

**(57) Abstract**

A temperature sensor circuit of a power semiconductor component comprises temperature-sensitive elements, some (Q1, and R1 to R3) of which are located in the vicinity of an active area of the component where heat is generated by the power semiconductor device (MPWR), whereas others (such as R4, R') are located more remote from the heat-generating active area and so are in a cool location. Hot-location elements (Q1, and R1 to R3) with different temperature coefficients are present in a first comparator circuit for indicating device temperature (Tabs) in the vicinity of the heat-generating active area. Both hot-location and cool-location elements (R2 and R4) are present in a second comparator circuit for indicating when a temperature gradient (Tdiff) threshold occurs. A circuit connection (5, 7) between the first and second comparator circuits, preferably at the inputs of their respective comparators (CP1, CP2) couples together the hot-location temperature-sensitive elements (Q1, R1, R2, R3) of the first and second comparator circuits so that the temperature gradient threshold sensed by the second comparator circuit decreases as a function of the device temperature (Tabs).

FOR THE PURPOSES OF INFORMATION ONLY

Codes used to identify States party to the PCT on the front pages of pamphlets publishing international applications under the PCT.

AL	Albania	ES	Spain	LS	Lesotho	SI	Slovenia
AM	Armenia	FI	Finland	LT	Lithuania	SK	Slovakia
AT	Austria	FR	France	LU	Luxembourg	SN	Senegal
AU	Australia	GA	Gabon	LV	Latvia	SZ	Swaziland
AZ	Azerbaijan	GB	United Kingdom	MC	Monaco	TD	Chad
BA	Bosnia and Herzegovina	GE	Georgia	MD	Republic of Moldova	TG	Togo
BB	Barbados	GH	Ghana	MG	Madagascar	TJ	Tajikistan
BE	Belgium	GN	Guinea	MK	The former Yugoslav Republic of Macedonia	TM	Turkmenistan
BF	Burkina Faso	GR	Greece	ML	Mali	TR	Turkey
BG	Bulgaria	HU	Hungary	MN	Mongolia	TT	Trinidad and Tobago
BJ	Benin	IE	Ireland	MR	Mauritania	UA	Ukraine
BR	Brazil	IL	Israel	MW	Malawi	UG	Uganda
BY	Belarus	IS	Iceland	MX	Mexico	US	United States of America
CA	Canada	IT	Italy	NE	Niger	UZ	Uzbekistan
CF	Central African Republic	JP	Japan	NL	Netherlands	VN	Viet Nam
CG	Congo	KE	Kenya	NO	Norway	YU	Yugoslavia
CH	Switzerland	KG	Kyrgyzstan	NZ	New Zealand	ZW	Zimbabwe
CI	Côte d'Ivoire	KP	Democratic People's Republic of Korea	PL	Poland		
CM	Cameroon	KR	Republic of Korea	PT	Portugal		
CN	China	KZ	Kazakhstan	RO	Romania		
CU	Cuba	LC	Saint Lucia	RU	Russian Federation		
CZ	Czech Republic	LI	Liechtenstein	SD	Sudan		
DE	Germany	LK	Sri Lanka	SE	Sweden		
DK	Denmark	LR	Liberia	SG	Singapore		
EE	Estonia						

DESCRIPTION

**POWER SEMICONDUCTOR DEVICES WITH A TEMPERATURE SENSOR
CIRCUIT**

5

This invention relates to power semiconductor components, for example a switch for automotive switching applications, comprising a power semiconductor device with a temperature sensor circuit. The power semiconductor device may be, for example, an insulated-gate field-effect transistor (hereinafter termed "MOSFET"), an insulated-gate bipolar transistor (hereinafter termed "IGBT"), or a bipolar transistor. The temperature sensor circuit can serve for sensing whether the device is approaching a thermal overload, and it may even be sufficiently sensitive for determining whether the device load is short-circuited.

15

United States Patent specification US-A-5,563,760 (our reference PHB 33667) discloses a temperature sensor circuit for such power semiconductor devices comprising hot-location and cool-location temperature-sensitive elements in a comparator circuit. The whole contents of US-A-5,563,760 are hereby incorporated herein as reference material. In particular, US-A-5,563,760 discloses a circuit sensing a temperature gradient (T_{diff}) threshold between the hot and cool locations. The circuit comprises (e.g. in Figures 5 and 6 of US-A-5,563,760) temperature-sensitive elements serially arranged in first and second parallel arms which form a Wheatstone bridge arrangement in a comparator circuit and which are fed by current sources derived from a PTAT (proportional-to-absolute-temperature) voltage. The biasing of the arms via their respective PTAT current sources is arranged to render the temperature gradient threshold sensed by the T_{diff} circuit either independent of the absolute (or actual) device temperature or a decreasing function of the device temperature based on a cool region of the device. The output of the comparator circuit provides a turn-off signal to the power semiconductor device

25

20

30

in the event of an excessive T_{diff} .

It is an aim of the present invention to provide an even more advantageous temperature sensor for a power semiconductor device, in which a T_{diff} threshold sensed by a comparator circuit can decrease as a function of the device temperature at a hot location of the device.

According to the present invention there is provided a power semiconductor component comprising a power semiconductor device with a temperature sensor circuit, wherein the temperature sensor circuit comprises hot-location temperature-sensitive elements in a first comparator circuit and hot-location and cool-location temperature-sensitive elements in a second comparator circuit, the hot-location temperature-sensitive elements being located in the vicinity of a heat-generating active area of the power semiconductor device, and the cool-location temperature-sensitive element (or elements) being located more remote from the heat-generating active area, the hot-location temperature-sensitive elements of the first comparator circuit have different temperature coefficients for indicating device temperature in the vicinity of the heat-generating active area, the second comparator circuit with both hot-location and cool-location temperature-sensitive elements serves for indicating when a temperature gradient threshold occurs between a hot location in the vicinity of the heat-generating active area and a cool location more remote from the heat-generating active area, and a circuit connection between the first and second comparator circuits which couples together the hot-location temperature-sensitive elements of the first and second comparator circuits and so makes the temperature gradient threshold indicated by the second comparator circuit into a decreasing function of the device temperature at a hot location.

In this context, "hot" and "cool" refer to locations with respect to the heat-generating active area of the power semiconductor device, namely that a "hot" element is in the vicinity of the heat-generating active area while the "cool" element is more remote from the heat-generating active area. So as to facilitate the subsequent discussion, the first comparator circuit which may

serve for indicating when a device temperature threshold is reached is herein designated the "Tabs circuit", the device temperature being designated "Tabs". Similarly the second comparator circuit which serves for indicating when a temperature gradient threshold occurs between a hot location in the vicinity of the heat-generating active area and a cool location more remote from the heat-generating active area is herein designated the "Tdiff circuit", the temperature gradient being designated "Tdiff".

The hot-location temperature-sensitive elements of different temperature coefficients in the Tabs circuit may have opposite, i.e. positive and negative, temperature coefficients. Very good Tabs sensitivity can then be achieved using well-established element technologies. Thus, for example, temperature-sensitive elements of positive temperature coefficient (herein designated "PTC") may be in the form of, for example, resistors and/or MOSTs, whereas those of negative temperature coefficient (herein designated "NTC") may be, for example, p-n junction diodes and/or bipolar transistors.

In a temperature sensor circuit in accordance with the invention, the hot-location temperature-sensitive elements of the Tdiff circuit may include hot-location temperature-sensitive elements of the Tabs circuit so as to make the temperature gradient threshold sensed at a comparator input of the Tdiff circuit a decreasing function of the device temperature at a hot location. By thus sharing hot-location temperature-sensitive elements, the total number of hot-location temperature-sensitive elements required can be kept low. Thus, the circuit connection which couples together the hot-location temperature-sensitive elements of the Tabs and Tdiff circuits may be at comparator inputs of Tabs and Tdiff circuits. The temperature-sensitive elements of both the Tabs and Tdiff circuits may be serially arranged in first and second parallel arms. Each arm can provide comparator inputs of both the Tabs and Tdiff circuits.

These first and second arms may form bridge arrangements of the Tdiff and Tabs comparator circuits and may be fed by current sources controlled by a PTAT (proportional-to-absolute-temperature) voltage. The PTAT voltage can be derived, in known manner, across a matched resistance of the same

temperature coefficient. The resulting temperature sensor circuit is both sensitive and reliable.

The first arm may comprise a first hot-location temperature-sensitive element of the Tabs circuit biased via a first hot-location temperature-sensitive
5 element of the Tdiff circuit, and the second arm may comprise a second hot-location temperature-sensitive element of the Tabs circuit biased via a cool-location temperature-sensitive element of the Tdiff circuit. In this case, the comparator inputs of the Tabs circuit may be taken from the series nodes of these elements in their respective arms, and the comparator inputs of the Tdiff
10 circuit may be taken from nodes of these arms with their respective PTAT current sources.

In a modified form, the second hot-location temperature-sensitive element of the Tabs circuit may be biased via a second hot-location temperature-sensitive element of the Tdiff circuit in series with the cool-location
15 temperature-sensitive element of the Tabs circuit, and one of the comparator inputs of the Tabs circuit may be taken from a node of this second hot-location temperature-sensitive element of the Tabs circuit with this second hot-location temperature-sensitive element of the Tdiff circuit.

A hysteresis feedback may be provided in the comparators of both the
20 Tabs and Tdiff circuits, or in at least one of them (e.g. the comparator of the Tabs circuit), so as to inhibit hunting or cycling of the temperature sensor circuit. Such hysteresis feedback may be provided in combination with any one or more of the other features of the present invention.

The comparator output of the Tdiff circuit in an arrangement in
25 accordance with the invention can be sufficiently sensitive to be used as a monitor for detecting an excessive temperature rise in the device due to its load becoming short-circuited, e.g. when most of a supply-to-ground voltage is directly across the power semiconductor device as a result of, for example, a lamp or bulb operated by the device having blown into a short-circuited
30 condition. However, the power device may have a specially designed short-circuit detector circuit.

The circuit features in accordance with the present invention, as well as additional circuit functions (if so desired) and their device features may be integrated with the power device using known integration and circuit techniques as described in, for example, US-A-4,929,884 and US-A-5,563,760 and/or with novel integrated device structures and techniques as disclosed herein. Thus, United States patent specification US-A-4,929,884 (our reference PHB 33363) discloses various monitor and/or protective circuits which are advantageous for such power semiconductor devices. The whole contents of US-A-4,929,884 are hereby incorporated herein as reference material.

These and other features in accordance with the present invention are illustrated specifically in embodiments of the invention now to be described, by way of example, with reference to the accompanying diagrammatic drawings, in which:

Figure 1 is a circuit diagram of one embodiment of a temperature sensor circuit of a power semiconductor component in accordance with the present invention;

Figure 2a is a plan view of a power semiconductor component in accordance with the present invention, illustrating one layout embodiment for hot-location and cool-location temperature-sensitive elements in relation to the power semiconductor device of the component;

Figure 2b is a cross-sectional view of the power semiconductor component on the line II-II of Figure 2a;

Figure 3 is an illustrative plot of T_{diff} in $^{\circ}C$ versus T_{abs} in $^{\circ}C$, showing typical examples in respective lines A and B of the temperature thresholds at which the T_{diff} and T_{abs} comparators CP1 and CP2 will trip in the Figure 1 circuit for the power semiconductor component of Figure 1;

Figures 4a to 4e are cross-sectional views of different parts of the semiconductor body of the power semiconductor component of Figure 1, illustrating how the circuit components of Figure 1 may be integrated with a power MOSFET or IGBT device using known DMOS technology; and

Figure 5 is a circuit diagram of a comparator with hysteresis, and suitable for use in the circuit of Figure 1.

It should be noted that the drawings are diagrammatic and not drawn to scale. Relative dimensions and proportions of the device parts of Figures 2 and 4 have been shown exaggerated or reduced in size, for the sake of clarity and convenience in the drawings.

Figure 1 illustrates one embodiment of a temperature sensor circuit of a power semiconductor component, for example a high side switch HSS for automotive switching applications. The circuit of Figure 1 monitors the thermal condition of the component to sense whether its power semiconductor device (MPWR in Figures 2a, 2b and 4a) is approaching a thermal overload, and it provides both Tabs and Tdiff output signals which can be used in known manner to protect the device MPWR against thermal overload by controlling the device operation.

The temperature sensor circuit of Figure 1 comprises hot-location temperature-sensitive elements Q1 and R1 to R3 in a first (Tabs) comparator circuit and both hot-location and cool-location temperature-sensitive elements R2 and R4 in a second (Tdiff) comparator circuit. The hot-location elements Q1, R1, R2 and R3 are located in the vicinity of an active area of the component where heat is generated by the power semiconductor device MPWR. The cool-location element or elements such as R4 are located more remote from the heat-generating active area. The elements Q1 and R1 to R2 of the first comparator circuit have different temperature coefficients for indicating when a device temperature (Tabs) threshold is reached. The second comparator circuit with both hot-location and cool-location temperature-sensitive elements R2 and R4 serves for indicating when a temperature gradient (Tdiff) threshold occurs between the hot location in the vicinity of the heat-generating active area and the cool location more remote from the heat-generating active area.

Hereinafter the first comparator circuit is designated the "Tabs circuit",

and the second comparator circuit is designated the "Tdiff circuit". The hot-location elements of the Tdiff circuit effectively include Q1, R1, R2, and R3 of the Tabs circuit to make the temperature gradient threshold sensed at the comparator inputs of the Tdiff circuit a decreasing function of the device temperature Tabs at a hot location. The elements R1-R2 and Q1-R3-R4 in the Figure 1 circuit are arranged in common arms of the Tabs and Tdiff circuits (via nodes 5 to 9), and the nodes of these arms provide a circuit connection between the Tabs and Tdiff circuits which couples together the hot-location temperature-sensitive elements of both the Tabs and Tdiff circuits and so makes the temperature gradient threshold indicated at the Tdiff circuit output into a decreasing function of the device temperature Tabs at the hot location. Thus, R1 and Q1,R3 provide an imbalance voltage (which is responsive to the absolute temperature Tabs of hot locations of the device) at the voltage-supply ends of R2 and R4. A temperature gradient between R2 and R4 can counter this temperature-sensitive imbalance voltage, and so the Tdiff threshold in the Tdiff circuit derates in real-time with Tabs.

This circuit is a novel way of optimally combining temperature sensitive elements to combine differential and absolute over-temperature detection functions so as to provide safe (near ideal) thermal protection for a power device MPWR while still allowing the device's inherent thermal capacity and transient load driving capability to be fully exploited.

Two main methods of thermal overload detection have been used previously. The first is an absolute temperature (Tabs) detector based on a sensor or multiple sensors which are close to or positioned within the power device area. An example is described in US-A-4,929,884 (our reference PHB 33363), the whole contents of which are hereby incorporated herein as reference material. The second is a differential temperature (Tdiff) sensor which detects the local temperature rise at the edge of the power device active area compared with some location further from the power device. Examples are described in US-A-5,563,760.

The first method has the disadvantage that, if the power device is initially

cool overall, then extremely large temperature gradients may be developed by overload conditions before the device can be turned off. In the case of repetitive overload conditions then these large temperature gradients can cause significant damage to the semiconductor body (chip) and its associated packaging/mounting hardware.

The second method effectively limits the maximum temperature gradient at a value which can safely be survived even if the device is initially hot overall. Unfortunately, this therefore limits the extent to which the thermal capacity of an initially cool device may be exploited, because of the need to protect warm or hot devices also.

A temperature-sensing circuit in accordance with the present invention combines these two functions Tabs and Tdiff in a circuit configuration, in which the actual temperature sensitive elements (such as Q1, R1 to R4) may also be shared in a common arrangement, for example as in the Figure 1 circuit. Whereas in US-A-5,563,760 it was envisaged to derate the Tdiff limit according to a cooler absolute temperature sensor, Tdiff in this new circuit is derated according to absolute temperature (Tabs) sensors Q1,R1 operating in the hot location. The combined Tdiff-Tabs circuit may include a band-gap reference circuit (for example the circuit block BGR of Figure 1) which can be of a known, fairly standard type. When hysteresis is included in this combined Tdiff-Tabs circuit, the hysteresis feedback is absent from the common sensor arrangement but can be provided within the comparator function.

Figure 1 illustrates a specific embodiment of the novel temperature sensing circuit, which has a Wheatstone bridge network comprising the temperature-sensitive resistances Q1 and R1 to R3 in hot locations (i.e near the power device MPWR) and the temperature-sensitive resistance R4 is in a cooler location (i.e more distant from the power device MPWR), see example in Figures 2a and 2b. In this specific example, Q1 is a NTC band-gap sensor, whereas R1 to R4 are PTC resistances. The first arm of the bridge comprises hot-location R1 of the Tabs circuit biased via hot-location R2 of the Tdiff circuit, and the second arm comprises hot-location Q1 of the Tabs circuit biased via

hot-location R3 in series with cool-location R4 of the Tdiff circuit. The Tabs circuit comprises a comparator CP1 having inputs taken respectively from the series node 5 of R1-R2 and from the series node 6 of Q1-R3. The Tdiff circuit comprises a comparator CP2 having inputs taken from the nodes 8 and 9 of R2 and R4 with their respective PTAT current sources M1 and M2.

The base of Q1 and one end of R1 are coupled to a first supply line 1 derived from a power line 3 at a voltage Vb. The opposite ends of these two arms of the bridge are fed by their respective PTAT current sources M1 and M2, through series resistors RM1, RM2 which are connected to a second supply line 2. The circuit of Figure 1 may be formed of low voltage semiconductor circuit components which are integrated monolithically with the high voltage power device MPWR using the circuit integration principles disclosed in US-A-4,929,884. Thus, the device substrate may be connected to a high voltage (Vb) terminal of the power supply (for example a battery), and the low voltage semiconductor circuit components of the Figure 1 circuit can operate from a low voltage supply Vlow which is regulated with reference to the high voltage terminal. Thus, the line 2 of Figure 1 is an artificial ground at Vlow, with line 1 at a more positive potential. In this case, the current sources M1 and M2 are actually sinks, drawing current through their respective first and second arms R1, R2 and Q1, R3, R4 of the bridge. The line 1 may be directly connected to the power line 3 and so be at the positive supply voltage Vb. However, it may be beneficial to set the line 1 at a lower voltage than Vb so as to centre the bridge output voltages (at nodes 5, 6, 8, 9) close to the ideal input range of each comparator CP1 and CP2. Thus, by way of example, Figure 1 illustrates reducing the voltage level of line 1 by a diode-connected MOST P6 coupled between the lines 3 and 1.

Current flow through the NMOSTs M1 and M2 forming these current sinks is controlled by a PTAT voltage Vref applied to their gates from a reference circuit, namely block BGR of Figure 1. The reference circuit BGR, operating at the same ambient temperature as the cooler areas of the chip, controls a precision voltage which is directly proportional to absolute

temperature (PTAT) and which is derived from across a resistor R' using a current sink, in a similar manner to the PTAT voltage source described in US-A-5,563,760. Thus, the reference circuit BGR comprises a bipolar transistor Q' having two emitters $E1$ and E_n , the effective emitter area of E_n being J times larger than that of $E1$, (for example, E_n may be composed of a plurality J of emitters each having the geometry and area of $E1$). For bipolar transistors with a low gain, there are several orders of magnitude (e.g. 6 decades) of emitter current I_e for which the base-emitter voltage V_{be} is a logarithmic function of I_e , the slope of which is directly proportional to temperature. Thus, by operating two similar-technology emitters $E1$ and E_n at different emitter current densities but with a fixed ratio, the difference dV_{be} in their V_{be} values is a constant directly proportional to absolute temperature. The emitter-base junctions of Q' act as NTC bandgap temperature sensors and respond in the same way to a temperature change as do the emitter-base junction of $Q1$, because both Q' and $Q1$ were fabricated in the same bipolar transistor process technology.

Emitter $E1$ of Q' is connected directly to a NMOST $M1'$ acting as a current sink via a series resistor $RM1'$ to the V_{low} line 2. Emitter E_n is coupled via a series resistor R' to a NMOST $M2'$ acting as a current sink with a series resistor $RM2'$. The voltage difference dV_{be} (the PTAT voltage) which occurs between $E1$ and E_n is impressed across the resistor R' , in the following manner. The resistor R' is fabricated in the same process technology as the resistors $R1$ to $R4$, $RM1$, $RM2$, $RM1'$, $RM2'$ so as to respond in the same way to a temperature change.

A differential amplifier A' takes inputs directly from the respective serial nodes of $R'-M2'$ and $E1-M1'$ and provides an output in the form of a voltage V_{ref} . The output of A' is connected to the gates of $M1$, $M2$, $M1'$ and $M2'$ to control the magnitude of current through $M1$, $M2$, $M1'$ and $M2'$ by means of V_{ref} . The feedback from $M1'$ and $M2'$ to the inputs (-) and (+) of A' ensures that the voltages at their nodes with R' and Q' $E1$ are equal. This means that the voltage difference dV_{be} (the PTAT voltage) is impressed across R' . The gate control of $M1$ and $M2$ by the output voltage V_{ref} of A' ensures that the

currents fed to the bridge arms R1,R2 and Q1,R3,R4 are proportional to those through M1' and M2'. Thus the voltage across the cool-location R4 is proportional to the voltage difference dV_{be} (the PTAT voltage) which is impressed across the cool-location R'. Furthermore, when the hot-location R1, R2, R3 are not hot (i.e. also at the same cool temperature as R' and R4), then the voltages across R1, R2, R3 are also proportional to the voltage difference dV_{be} (the PTAT voltage) which is impressed across R'.

Other PTAT voltages scaled to any absolute magnitude can be generated by using the Vref output of A' to control another matched or ratioed current sink or source (in a similar manner to M1 and M2) drawing current through a matched or ratioed resistor (in a similar manner to RM1, RM2, and R1 to R4, as compared with R'). Thus, the control voltage Vref for current sink elements is distributed also to other circuits of the power semiconductor component, so that any circuit containing similar matched or ratioed current sink elements and a matched or ratioed resistor of this particular type can be used to generate further PTAT voltages of different magnitudes. The circuit block BGR illustrates one specific example of PTAT reference circuit, and it will be evident that other known forms of PTAT reference circuit may alternatively be used with a combined Tabs and Tdiff circuit in accordance with the invention.

Both the line 1 of Q1,R1 and base line 1' of Q' can be individually set to appropriate potentials to match the respective input working ranges of A', CP1 and CP2. Thus, the base of Q' may be connected directly to the power line 3, or it may be coupled indirectly (for example, by a diode-connected MOST P6') to provide more suitable voltage input levels for amplifier A'. Preferably, M1', M2', M1, and M2 are coupled to the line 2 by source degeneration resistors RM1', RM2', RM1, and RM2 of suitable magnitude to operate these MOST current sinks with an approximately zero temperature coefficient, so that the actual location of these Mx,RMx networks in cool areas (remote from MPWR) is not critical. The geometries of M1', M2', M1, and M2 are ratio-matched, as are RM1', RM2', RM1, and RM2.

Particular operational features of this Figure 1 circuit in accordance with the invention are:

Tabs part

5 In the new temperature sensor circuit, R1 is biased using the above technique to have a PTAT voltage across it; Q1, which is of the same bipolar transistor type as the band-gap ratioed emitters of bipolar device Q' in the reference circuit BGR, has a base-emitter voltage V_{be} which reduces with absolute temperature. The magnitude of R1 and the geometries of M1, RM1 and Q1, M2, RM2 are chosen such that the PTAT voltage across R1 and the
10 base-emitter voltage of Q1 become equal at the desired absolute trip temperature (Tabs, e.g. 165°C).

The Tabs comparator CP1 comparing these voltages at its inputs (-) and (+) provides an output signal Tabs indicating that an absolute over-temperature condition has occurred. This output signal Tabs enables the power device
15 MPWR to be turned off and a status signal issued. Once this transition occurs, the Tabs comparator CP1 may force an input offset to provide hysteresis of a few tens of millivolts so as to maintain its status signal and inhibit temperature cycling or hunting. The over-temperature status signal will remain active until the sensors R1 and Q1 cool slightly, e.g. by 10°C, at which point the control
20 logic may turn the power device MPWR on again.

Tabs derating for Tdiff

The potentials at the lower end of R1 and Q1 (i.e their respective nodes 5 and 6 with R2 and R3) are arranged to be equal at the desired absolute trip temperature Tabs.

25 The potentials at the lower end of R1 and R3 (i.e their respective nodes 5 and 7 with R2 and R4) do not become equal until some higher temperature, e.g. 200°C. The imbalance at these nodes 5 and 7 is used as the built-in offset of the Tdiff bridge formed by R2 and R4. The temperature where this imbalance derates to zero is well defined with respect to the normal Tabs trip
30 point, being based on the values of resistance and PTC temperature coefficient of the precision absolute temperature sensors R1 and Q1 and the further

matched resistor R3. Thus, R3 adds a small PTAT voltage to the Vbe voltage of Q1 (which is the same effect as subtracting some PTAT voltage from the drop across R1) so that a little of the NTC of Q1 is compensated by the PTAT voltage across PTC R3. Voltage balance of node 7 at the bottom of R3 with
5 node 8 at the bottom of R2 is therefore reached at a higher temperature than the balance of nodes 6 and 5.

Tdiff part

When the current sinks M1, RM1 and M2, RM2 are equal, then the Tdiff operation can be understood in terms of a matched R2 and R4. However,
10 when the current sinks M1, RM1 and M2, RM2 are ratioed (e.g. with the channel width of M1 being three times that of M2 and the resistor width of RM1 being three times that of RM2) then the geometry (and hence resistance values) of R2 and R4 are also ratioed according to their respective current sink elements M1, RM1 and M2, RM2, so as to arrange that R2 and R4 have the same voltage
15 across them when there is no differential temperature gradient Tdiff between them. At any given absolute (hot location) temperature, the imbalance voltage at the tops of R2 and R4 (nodes 5 and 7) divided by the average voltage across R2 and R4 and divided by the temperature coefficient of the resistors R2 and R4 determines the differential temperature difference, Tdiff, which will
20 bring the lower nodes 8 and 9 of R2 and R4 back to equal potentials. The comparator CP2 compares these two voltages at nodes 8 and 9 and signals if this condition is exceeded. Again hysteresis may be applied allowing the power device MPWR to automatically re-start when the temperature gradient Tdiff falls, or the output may be used to latch the device MPWR off until an
25 external reset signal is received.

The Tdiff value at which CP2 will trip is a direct function of the actual absolute temperature Tabs at the hot sensors, for example as illustrated in Figure 3. The horizontal Tabs axis corresponds to the actual device temperature at the hot locations of (and sensed by) Q1, R1, R2 and R3. The
30 vertical Tdiff axis corresponds to the actual difference in temperature between (and sensed by) the hot-location R2 (and Q1, R1 and R3) and the cool-location

R4. The line B illustrates the temperature along the horizontal axis at which the Tabs comparator CP1 trips, as described above. This Tabs trip temperature (165°C in this example) is independent of Tdiff. The line A illustrates the variation in the differential temperature at which the Tdiff comparator CP2 trips, which is a function of Tabs. Thus, as can be seen from Figure 3, CP2 trips at a higher Tdiff (e.g. 65°C) when Tabs is low (e.g. at room temperature, 25°C) but at a lower Tdiff (e.g. 15°C) when Tabs at the hot location is high (e.g. at 165°C). Thus, the allowable Tdiff depends on the temperature at the hot location and is constantly adjusted according to the absolute hot sensors Q1,R1,R2,R3.

In many cases, a large inrush of current into a power device MPWR is needed in order to switch a load (such as a lamp or a motor when stationary) which is difficult to start. The temperature sensor circuit of Figures 1 to 3 is able to cope well with such an inrush, while also protecting the device. As can be seen from Figure 3, an initially overall cool (e.g. 25°C) device MPWR can operate with a large current inrush generating a large differential temperature (of e.g. 65°C) before tripping the Tdiff detector. With appropriate positioning of the hot and cool sensors Q1, R1 to R4, this trip level can equate to a peak temperature, deep within the active area of the power device, of about 200°C, but the Tabs circuit will trip if the Tabs average temperature at the periphery of the active device area exceeds, e.g. 165°C, so that there is no damage or malfunction of the power device MPWR and logic circuitry. Thus, a large inrush can be handled from a start condition (low Tabs). The large inrush producing this trip level is smaller than that which would trip a prior art circuit sensing Tabs alone, because in such a prior art circuit the peak temperature in the power device area might be well over 200°C before peripheral or embedded "hot" sensors reach a 165°C trip point. Thus, with the Tabs-only approach of the prior art so much thermal energy may be stored in the power device MPWR that logic circuits in control areas of the device may suffer malfunction or damage due to heat later spreading to these circuits from the power device area, even if the power device itself is not harmed.

At higher temperatures closer to the Tabs trip point the circuit trips at lower T_{diff} values to ensure again that excessive peak temperatures cannot occur in the power device area. The thickness t (see Figure 2) of the device chip affects the extent to which heat flows laterally from the power device area to surrounding circuitry before being efficiently sunk by vertical heat flow across thickness t to the chip support. Typically the cool location for R4 is at a distance d_2 (away from the active power device area) which is comparable to the thickness t . The hot locations for Q1, R1, R2, R3 is at a much closer distance d_1 , for example between $t/5$ and $t/4$. With suitable lateral positioning of the hot and cool sensors according to the thickness t of the chip, the arrangement can be such that it effectively imposes an extrapolated safe peak temperature limit within the power device active area of e.g 200°C. Typically the thickness t is about 0.25mm for a MPWR in the form of a vertical power MOSFET or IGBT. The power MOSFET or IGBT may have a heat-generating, active surface area of, for example, 10mm² consisting of, for example, tens of thousands of parallel cells. The hot locations for the sensors Q1, R1, R2, R3 may be a distance d_1 of about, for example, 50 μ m from the periphery of the MPWR active surface area. The cool location for R4 may be a distance d_2 of about, for example, 200 μ m away. The other circuit components such as M1, M2, RM1, RM2, Q', R', M1', M2', ... etc. are located no closer to the MPWR active surface than R4.

Thus, the resistance value of the various resistors are chosen as follows, in accordance with the current levels through the different arms. The value of PTC resistor R1 is chosen to give, at the Tabs trip temperature, a voltage drop at node 5 which balances that at node 6 of the NTC Q1. The resistance values of R2 and R4 may be chosen to give the same voltage drop across R2 and R4 when R2 and R4 are at the same temperature (thus $R_2 = R_4$, if the same current flows through R2 and R4; but $R_2 =$ a third of R_4 , when the current through R2 is three times that through R4). The small PTC resistor R3 is of a value sufficient to give a voltage drop providing the built-in offsets of the T_{diff} bridge. In a specific example of the Q1,R1-R4 bridge the

geometries of the current sink MOSTs M1 and M2 and their source resistors RM1 and RM2 may be ratio-matched to give a current (3I) through M1 which may be 3 times that (I) through M2; in this specific example, R1 to R4 may then have the following resistance values at room temperature: R1 9k Ω , R2 30k Ω ,
 5 R3 6k Ω , and R4 90k Ω , whereas RM1 may be 15k Ω , and RM2 may be 45k Ω . The value of R' may be, for example, 7k Ω , with an emitter ratio for Q' of, for example, 14 to 1.

In a modification of the Figure 1 circuit which is also in accordance with the present invention, there is no R3 between R4 and Q1, so that the hot Q1
 10 is fed directly from the cool R4, and the comparator input (+) of the CP1 is taken from a common node 6,7 of Q1 and R4. In this case, the resistance value of R4 is made slightly higher than that of R2, in order to compensate for the absence of the small-value R3. This results in a slight compromise in performance, which can be acceptable in some situations.

Figure 5 illustrates one example of a comparator circuit suitable for use
 15 as the comparator CP1 and/or CP2, i.e for both or either of the Tabs and Tdiff circuits of Figure 1. The comparator includes a hysteresis feedback from its Tabs or Tdiff output, in order to inhibit hunting or cycling of the temperature sensor circuit of Figure 1. This hysteresis feedback is achieved in the Figure
 20 5 circuit (via an optional Schmitt trigger SMT in series with the comparator output) to a shift input stage NShft of the comparator, so as to increase the conductance of MC3. In the Figure 5 circuit, MC4, MC5, MC7, MC8, MC10 and MC12 are n-channel enhancement MOSTs, whereas MC1a, MC1b, MC2a, MC2b, MC3, MC6, MC9 and MC11 are p-channel enhancement MOSTs. In the
 25 following description the transistors are functionally grouped together using the "+" symbol and are designated using appropriate terminology describing their circuit function. The positive potential on the voltage supply rail 1''/3 may be that of power line 3 or an appropriately lower-potential voltage line 1'' (as already described for lines 1 and 1' in Figure 1).

30 The operation of the Figure 5 comparator can be best understood by first neglecting the effect of MC1a/b and MC2a/b (as if MC1a/b and MC2a/b were

absent, or as if MC1a/b and MC2a/b were considered to be non-conducting). The parallel pair MC5 + MC8 sink a quiescent current for the common-source comparator pair MC4 + MC7 which in turn they draw from the mirror pair MC3 + MC6. Thus MC5, MC8, MC4, MC7, MC3 and MC6 form a classical differential amplifier core. An inverter comprises MC9 and MC10, and a further inverter comprises MC11 and MC12. The threshold of MC9 is matched to the thresholds of the mirror pair MC3 + MC6 by virtue of the relative geometries of MC9 to MC3 + MC6 and of MC10 to MC5 + MC8, so that the mirror pair MC3 + MC6 and the comparator input pair MC4 + MC7 must be exactly in balance with inputs (+) and (-) at equal potentials in order to bias the inverter in its active switching region. Similarly the threshold of MC11 is matched to the preceding threshold of MC9. The inverter MC9 + MC10 is a classical method of obtaining a single ended output from the classical differential amplifier core. The inverter MC11 + MC12 adds sufficient gain that the threshold mismatch of the following buffer (Schmitt trigger SMT) compared to the MC3 and MC6 thresholds, causes very little offset error at the input. For example the differential amplifier core MC3 to MC8 may have a differential gain of, for example, 100, and the first and second inverters may each have a gain of, for example, 10. So the input hysteresis and threshold mismatch voltages of SMT, compared to the preceding inverters, cause an input offset voltage which is just one ten thousandth in magnitude, and a mismatch of, for example, 1V would at the (+) and (-) inputs be equivalent to a 100 gV offset.

Thus, neglecting MC1a/b and MC2a/b the circuit function is simply a precision low offset comparator with a very small input hysteresis.

In the case where the (+) input is at a significantly higher potential than the (-) input, then the output (T_{abs}/T_{diff}) will be at the positive rail and the PMOSTs MC2a and MC2b will therefore be off. In this condition PMOSTs MC1a and MC1b can have no effect on the mirror MC3 + MC6. If the two inputs (-) and (+) are driven closer together then the overall circuit state remains much the same until the inputs become so close that the inverters MC9 + MC10 and MC11 + MC12 enter their active switching regions. The

input offset of the overall comparator is very small in this state.

However, once the inputs are considered to have passed each other, such that the (+) input is at a higher potential than the (-) input, then the SMT input and output will swing to the negative Vlow rail 2 and the PMOSTs MC2a and MC2b will be rendered conducting. It is now that the effect of MC1a/b and MC2a/b must be considered. The gates and sources of MC1a and MC1b are connected directly to the gates and sources of mirror pair MC3 + MC6. When MC2a and MC2b are in the ON state, then the drains of MC1a and MC1b are also connected effectively in parallel with the drain of MC3 in the mirror pair MC3 + MC6. Thus the mirror ratio of mirror MC3 and MC6 is no longer 1:1 but may be, for example, 2:1 with 2/3 of the comparator core quiescent current flowing in the MC3 side and 1/3 flowing in the MC6 side. These now unbalanced currents determine the respective thresholds of the input MOSTs MC4 + MC7 of the differential amplifier core such that the threshold of MC7 is now lower than the threshold of MC4 by an amount depending on the ratio of currents and their gain, for example by 30mV. Thus, once the inputs have passed each other, a large input offset is assumed by the comparator, so as to give effect to a hysteresis loop of Figure 5, with MC2a/b on in one state and off in the other state. An advantage in feedback coupling via the Schmitt trigger SMT, rather than a direct coupling, is to ensure that when approaching the balanced condition there can be no gradual turn on of MC2a/b (which might create a slight offset); instead MC2a/b are held completely off until the Schmitt trigger SMT changes its output state.

Figures 4a to 4e illustrate (by way of cross-sectional views of different parts of a semiconductor body 100) how the circuit components which may be used in the circuits of Figures 1 and 5 may be integrated with a power MOSFET or IGBT device (MPWR) using known DMOS technology in a manner similar to that in US-A-4,929,884.

A specific example is illustrated using conventional DMOS technology to form a power MOSFET or IGBT device of the n-channel enhancement-mode type. In this case, the semiconductor body 100 comprises a relatively lowly-

doped n-type silicon epitaxial layer 100b (N-), which forms the drain drift region of the MOSFET or IGBT device, and which is provided on a single-crystal silicon substrate 100a of relatively highly-doped n-type (for the MOSFET) or p-type (for the IGBT). One source cell of the device MPWR is shown in Figure 4a.

The source cell is of known type comprises, adjacent one major surface of the semiconductor body region 100b, a p-type transistor-body region 14 which contains a highly-doped n-type (N+) source region 17. In a low-doped (P) part 14b of the region 14 between the regions 17 and 100b there is a conduction channel area under the insulated gate 18 of the power MOSFET or IGBT device. This gate 18 may be a doped polycrystalline silicon layer, designated PS. As shown, the p body region 14 of the cell also has a central highly-doped (P+) subsidiary region 14a which is shorted to the source/cathode electrode S of the power device to inhibit parasitic bipolar action. The source/cathode electrode S and gate electrode G (not shown) are formed by metallisation m provided on top of an insulating layer 30 and making contact to the N+ source region 17 and insulated gate 18, respectively, via appropriate contact holes. The drain/anode electrode D is provided on the other major surface of the semiconductor body 100.

Figure 4b shows an example of a possible structure for an enhancement mode p-channel MOST, for example P6 and P6' of Figure 1, and MC1 to MC3, MC6 MC9 and MC11 of Figure 5, such as may be fabricated using this DMOS technology. The MOST has p conductivity type source and drain regions 40 and 41 (P with P+ contact regions) which are formed by doping an area of the N- region 100b in both the low-doped (P) and highly-doped (P+) p-type doping stages for the power transistor-body parts 14a and 14b. Its gate of polysilicon PS is formed in the same process steps as the gate 18 of the power transistor. Parts of the metallisation pattern m form its source, gate and drain connectors.

Figure 4c shows an example of a possible structure for an enhancement mode n-channel MOST, for example the MOSTs MC5, MC8, etc of Figure 5, such as may be fabricated using this DMOS technology. The MOST is formed

in a p-type well P formed in an area of the N- region 100b in the low-doped p-type doping stage for the power transistor-body part 14b. In this p-type well P, n-type source and drain regions (N with N+ contact regions) are formed by doping in an extra low-doped (N) n-type doping stage and the highly-doped (N+) n-type doping stage for the power transistor source region 17. Its gate of polysilicon PS is formed in the same process steps as the gate 18 of the power transistor.

Figure 4d shows an example of a possible structure for an n-p-n bipolar transistor, for example Q1, Q' of Figure 1, such as may be fabricated using this DMOS technology. An area of the N-region 100b forms the collector region of the transistor, together with a N+ contact region. A base region b is formed in this area of the N- region 100b in the high-doped P+ p-type doping stage for the power transistor-body part 14a. In this P+ p-type base region b, an n-type emitter region e is formed by doping in the highly-doped N+ n-type doping stage for the power transistor source region 17.

Figure 4e shows an example of a possible structure for the PTC resistors R1, R2, etc. of the Figure 1 circuit, such as may be fabricated using this DMOS technology. In this particular example the resistor has a resistance region 25' (P) which is formed by doping an area of the N- region 100b in the low-doped p-type doping stage for the power transistor-body part 14b; and contact regions P+ are formed in the same process steps as the highly-doped power transistor-body part 14a and are contacted by metal connections m. The resistor may include a top plate 50 formed by doped polysilicon (PS) on a dielectric film on the resistance region 25' in the same process steps as the power transistor gate 18 on the gate dielectric of the power transistor MPWR. The plate 50 acts as an electrostatic screen which is connected to the most negative contact of the resistor by its metal connection m. However, the resistance region 25' may be formed by doping an area of the N- region 100b in the high-doped p-type (P+) doping stage for the power transistor-body part 14a. Alternatively, instead of using the p-type doping, resistance regions may be formed with n-type conductivity by using, for example, the N+ doping stage

used to provide the source regions 17. These n-type resistance regions can be formed in a p-type well formed using the P doping stage of 14b. Thus, the resistors in a circuit in accordance with the invention may be formed as n-type resistance regions. Furthermore, instead of a doped resistance region 25' within the semiconductor body portion 100b, all of these PTC resistors may alternatively be formed in known manner as so-called thin-film resistors from a doped polycrystalline film deposited on top of the insulating layer on the semiconductor body portion 100b.

Although Figure 4a illustrates a planar cellular geometry for the induced channel and the gate 18 along a major surface of the body 100, various known forms of so-called "trench-gate" geometry may be used for MOSFETs and IGBTs, in which the insulated gate 18 is present in a trench in the major surface of the semiconductor body 100, between neighbouring cells in the region 100b. In this case, the channel (induced in transistor-body region 14b) extends vertically along the side walls of the trench. It will be evident that the temperature sensor circuits of Figure 1 (and alternative embodiments in accordance with the invention) may be integrated with a power semiconductor device MPWR of planar geometry as illustrated in Figure 4(a) or, for example, of trench-gate geometry.

In the embodiment of Figure 1, the circuit connection which couples together the hot-location temperature-sensitive elements of the Tabs and Tdiff circuits is at comparator inputs of both the Tabs and Tdiff circuits. Thus, in this preferred embodiment, the hot-location temperature-sensitive elements of the Tdiff circuit effectively include the hot-location temperature-sensitive elements Q1, R1, R2, and R3 of the Tabs circuit so as to derate the temperature gradient Tdiff threshold sensed at a comparator input of the Tdiff circuit as a function of the device temperature at a hot location. However, the circuit connection which couples together the hot-location temperature-sensitive elements of the Tabs and Tdiff circuits to provide the required derating may be made at the output of at least a Tabs-sensing circuit, instead of being at comparator inputs of both the Tabs and Tdiff circuits. This modified type of temperature sensor

circuit of a power semiconductor component in accordance with the present invention comprises separate Tabs and Tdiff circuits (i.e. without the temperature-sensitive elements of the Tabs circuit being directly connected to the temperature-sensitive elements of the Tdiff circuit), and so is less
5 advantageous in requiring more temperature-sensitive elements and more layout area than the Figure 1 circuit.

In one form of this modified type of circuit, the output of the Tabs-sensing circuit may be fed to an input of the comparator CP2 of the separate Tdiff circuit to provide the required derating of the Tdiff threshold via the input
10 of CP2. In different form of this modified type of circuit, the separate outputs of the Tabs-sensing circuit and the Tdiff comparator CP2 of the separate Tabs and Tdiff circuits may be fed (possibly via respective amplifier circuits to adjust their relative signal levels) to a summation circuit to provide the required derating of the Tdiff threshold at the output of the summation circuit.

15 Embodiments of the invention have been described for a High Side Switch HSS in which both the power semiconductor device MPWR and the temperature sensor circuit are powered from the voltage supply line 3. However, the same combined Tabs and Tdiff circuit principles in accordance with the invention may be used in a Low Side Switch (LSS), in which the power
20 device MPWR is located on the ground side of its load.

Thus, in summary, the present invention provides particularly a power semiconductor device and/or temperature sensor circuit having any one or more of the novel features herein described and/or illustrated in the drawings.

From reading the present disclosure, other modifications and variations
25 will be apparent to persons skilled in the art. Such modifications and variations may involve equivalent features and other features which are already known in the art and which may be used instead of or in addition to features already disclosed herein. Although claims have been formulated in this Application to particular combinations of features, it should be understood that the scope of
30 the disclosure of the present application includes any and every novel feature or any novel combination of features disclosed herein either explicitly or

implicitly and any generalisation thereof, whether or not it relates to the same invention as presently claimed in any Claim and whether or not it mitigates any or all of the same technical problems as does the present invention. The Applicants hereby give notice that new claims may be formulated to such features and/or combinations of such features during prosecution of the present application or of any further application derived therefrom.

CLAIMS

1. A power semiconductor component comprising a power semiconductor device with a temperature sensor circuit, wherein the temperature sensor circuit comprises hot-location temperature-sensitive elements in a first comparator circuit and hot-location and cool-location temperature-sensitive elements in a second comparator circuit, the hot-location temperature-sensitive elements being located in the vicinity of a heat-generating active area of the power semiconductor device, and the cool-location temperature-sensitive element(s) being located more remote from the heat-generating active area, the hot-location temperature-sensitive elements of the first comparator circuit have different temperature coefficients for indicating device temperature in the vicinity of the heat-generating active area, the second comparator circuit with both hot-location and cool-location temperature-sensitive elements serves for indicating when a temperature gradient threshold occurs between a hot location in the vicinity of the heat-generating active area and a cool location more remote from the heat-generating active area, and a circuit connection between the first and second comparator circuits which couples together the hot-location temperature-sensitive elements of the first and second comparator circuits and so makes the temperature gradient threshold indicated by the second comparator circuit into a decreasing function of the device temperature at a hot location.

2. A power semiconductor device as claimed in Claim 1, wherein the hot-location temperature-sensitive elements of different temperature coefficients in the first comparator circuit have opposite, i.e. positive and negative, temperature coefficients.

3. A power semiconductor device as claimed in Claim 1 or Claim 2, wherein the temperature-sensitive elements of both the first and second comparator circuits are serially arranged in first and second parallel arms.

4. A power semiconductor device as claimed in Claim 3, wherein the first and second arms form bridge arrangements for the first and second comparator circuits and are fed by current sources controlled by a PTAT (proportional-to-absolute-temperature) voltage.

5

5. A power semiconductor device as claimed in Claim 3 or Claim 4, wherein the first arm comprises a first hot-location temperature-sensitive element of the first comparator circuit biased via a first hot-location temperature-sensitive element of the second comparator circuit, and the second
10 arm comprises a second hot-location temperature-sensitive element of the first comparator circuit biased via a cool-location temperature-sensitive element of the second comparator circuit.

6. A power semiconductor device as claimed in Claim 5, wherein
15 comparator inputs of the first comparator circuit are taken from a node of the said first hot-location temperature-sensitive elements of the first and second comparator circuits and from a node of the second hot-location temperature-sensitive element of the first comparator with the cool-location temperature-sensitive element of the second comparator circuit, and wherein
20 comparator inputs of the second comparator circuit are taken from nodes of the first hot-location temperature-sensitive element and the cool-location temperature-sensitive element of the second comparator circuit with their respective PTAT current sources.

25 7. A power semiconductor device as claimed in Claim 5, wherein the second hot-location temperature-sensitive element of the first comparator circuit is biased via a second hot-location temperature-sensitive element of the second comparator circuit in series with the cool-location temperature-sensitive element of the second comparator circuit, and wherein comparator inputs of the first
30 comparator circuit are taken from a node of the said first hot-location temperature-sensitive elements of the first and second comparator circuits and

from a node of the second hot-location temperature-sensitive element of the first comparator circuit with the second hot-location temperature-sensitive element of the second comparator circuit, and wherein comparator inputs of the second comparator circuit are taken from nodes of the first hot-location
5 temperature-sensitive element and the cool-location temperature-sensitive element of the second comparator circuit with their respective PTAT current sources.

8. A power semiconductor device as claimed in Claim 1, wherein a
10 hysteresis feedback is provided in the comparator of the first comparator circuit, so as to inhibit hunting or cycling of the temperature sensor circuit.

9. A power semiconductor device as claimed in Claim 8, wherein a
15 hysteresis feedback is provided also in the comparator of the second comparator circuit, so as to inhibit hunting or cycling of the temperature sensor circuit.

1/4

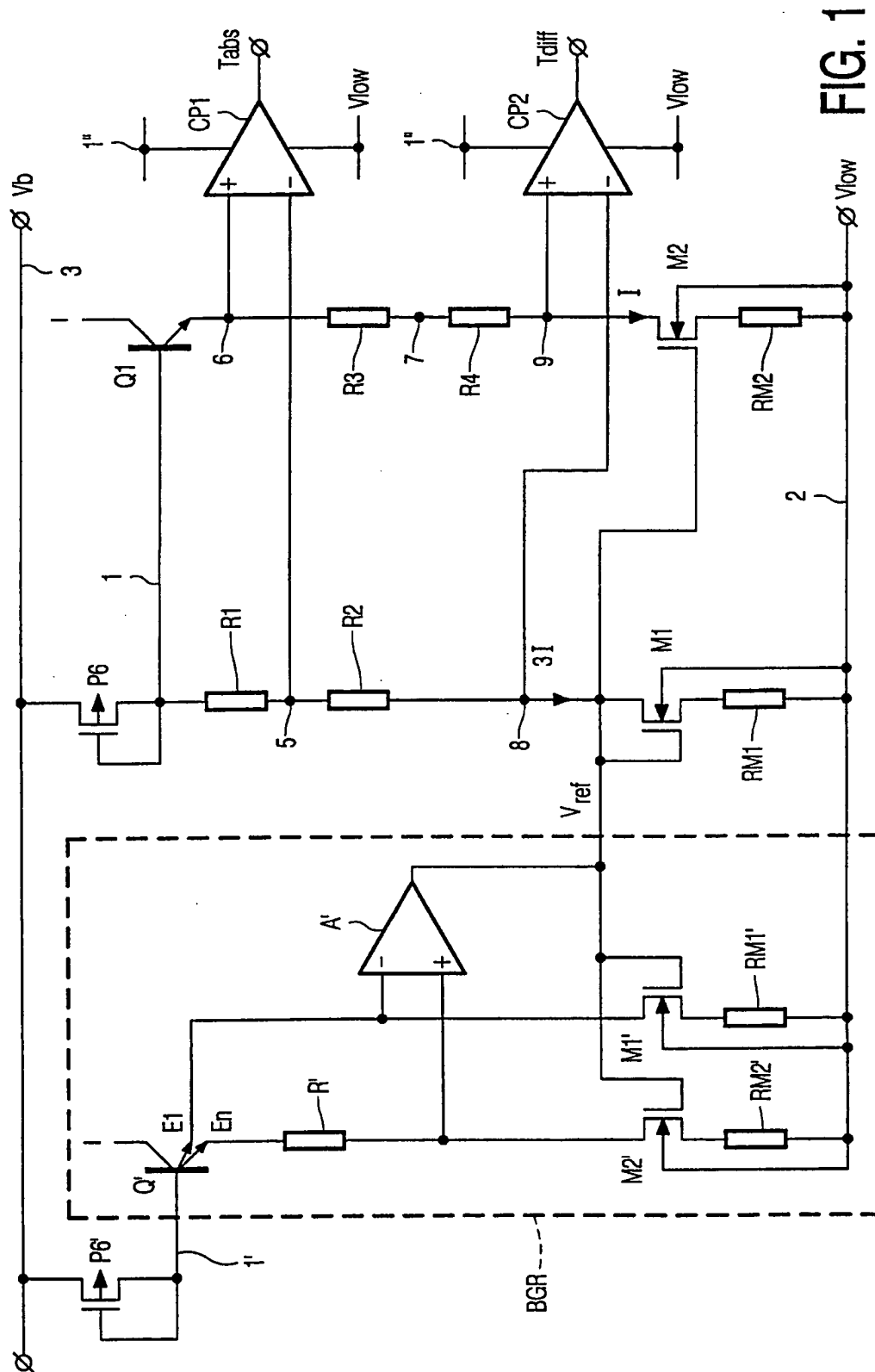


FIG. 1

2/4

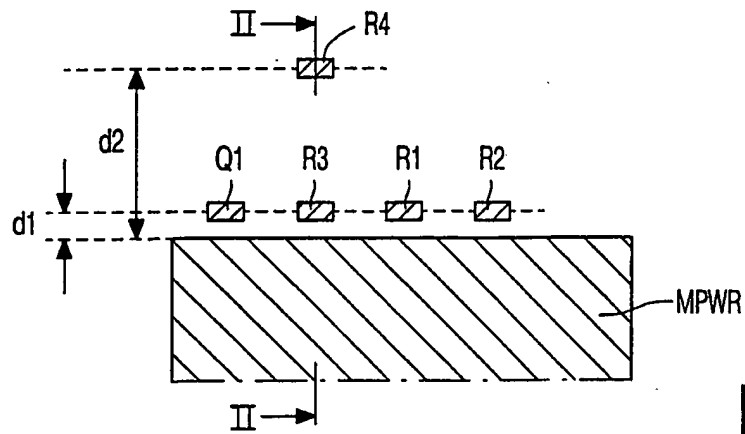


FIG. 2a

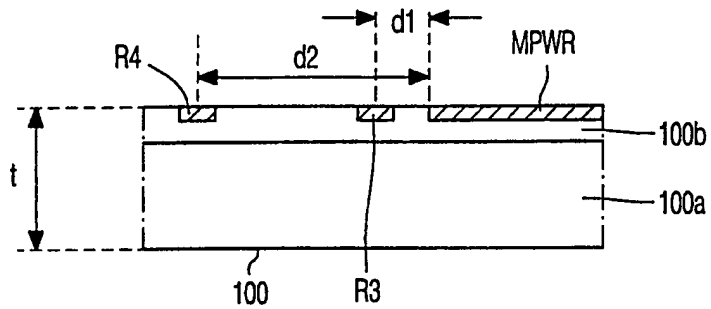


FIG. 2b

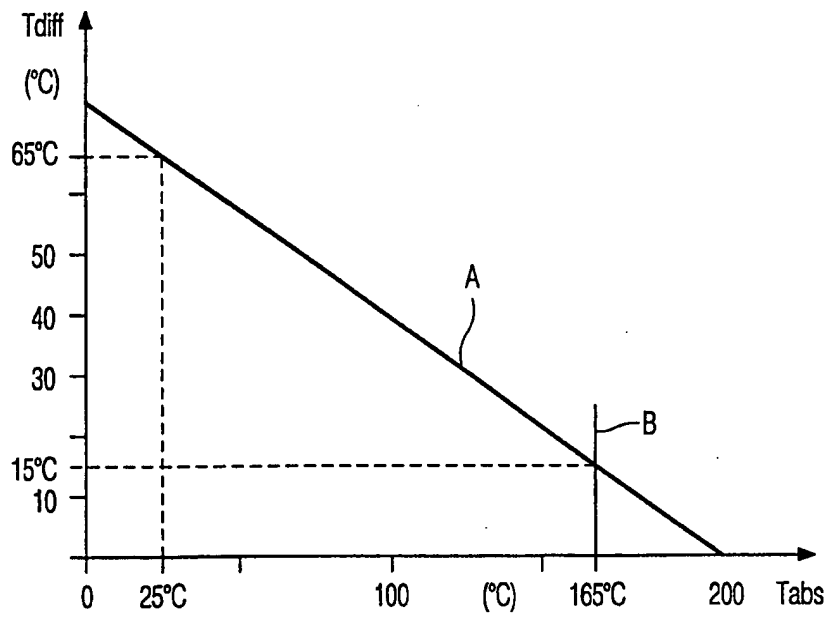


FIG. 3

3/4

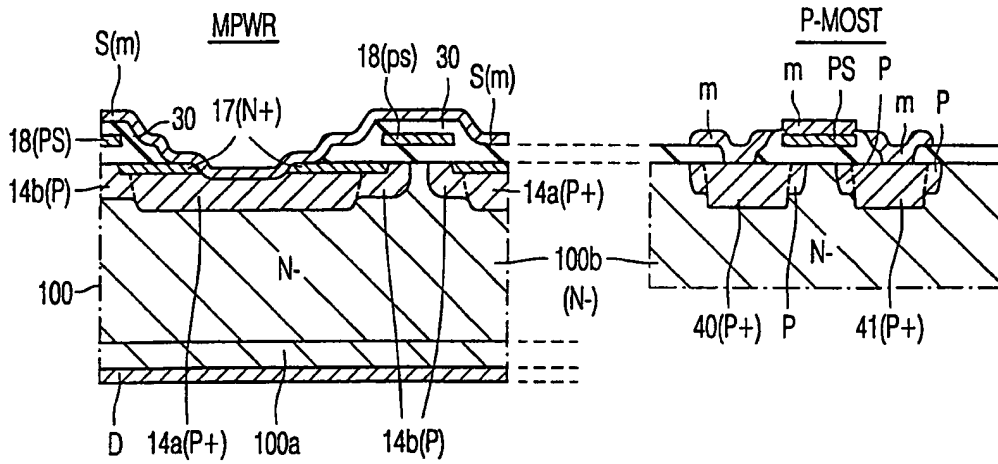


FIG. 4a

FIG. 4b

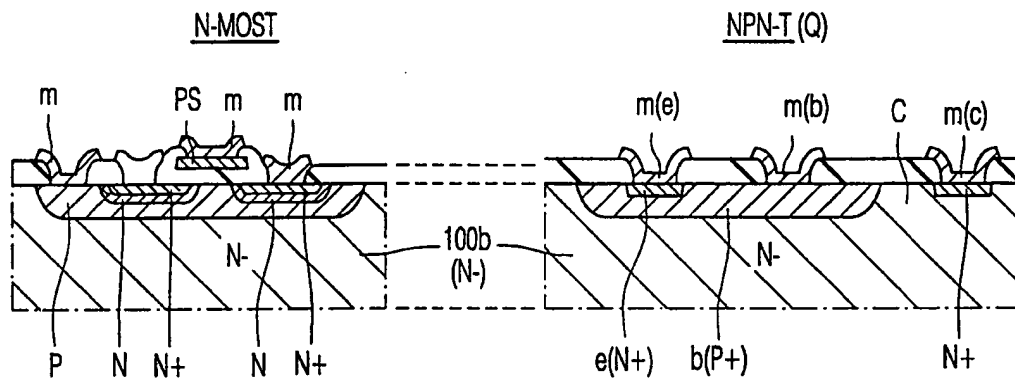


FIG. 4c

FIG. 4d

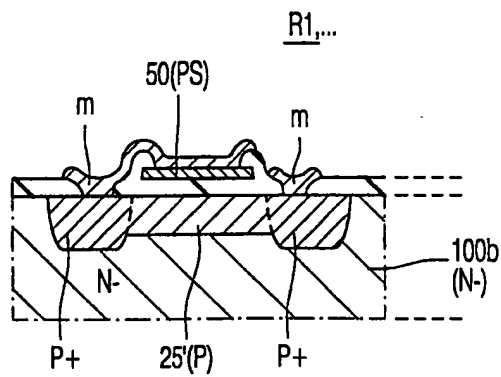


FIG. 4e

4/4

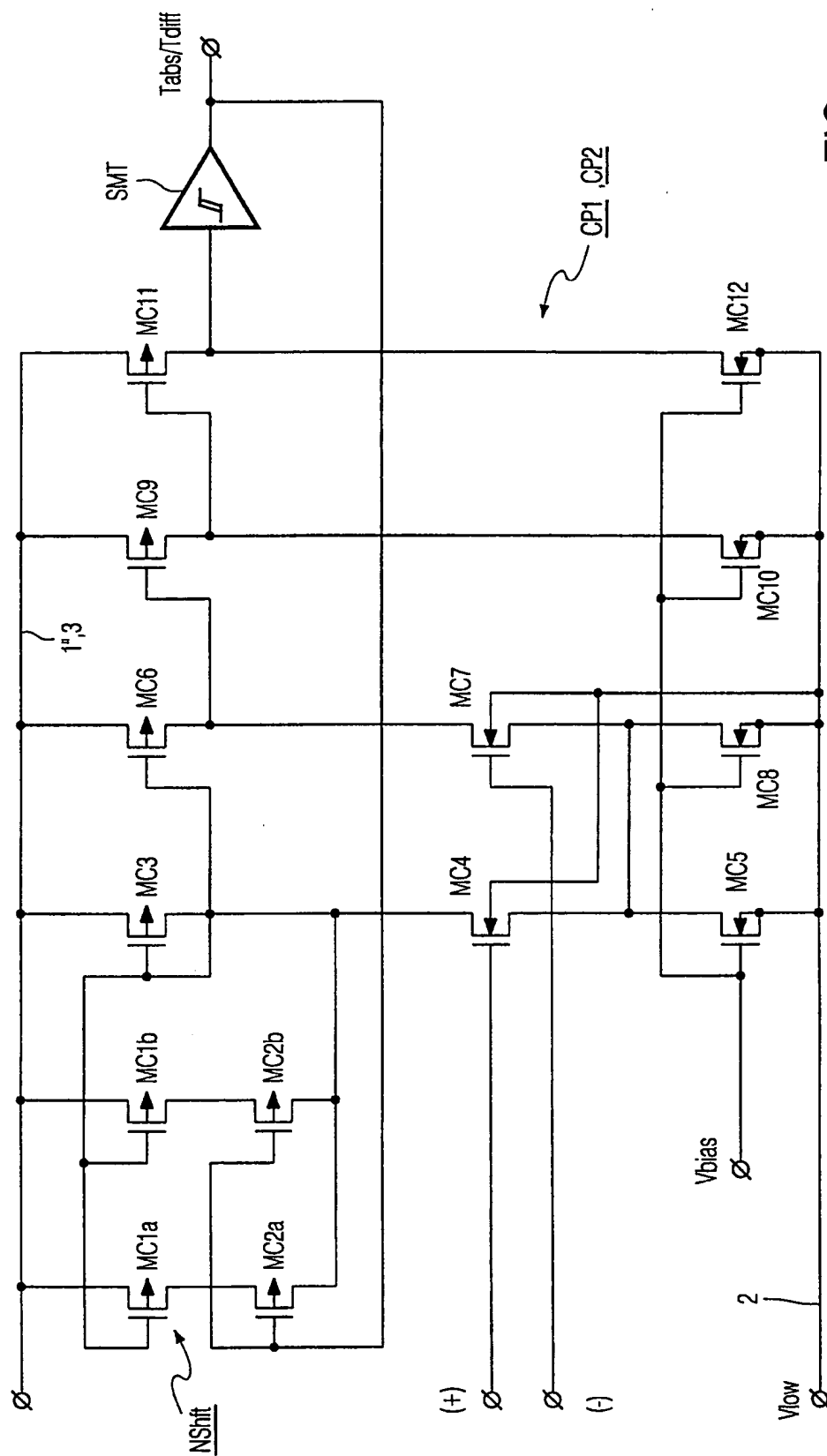


FIG. 5

12

EUROPEAN PATENT APPLICATION

21 Application number: 88201458.2

51 Int. Cl.4: B60R 16/02 , B60J 1/17

22 Date of filing: 09.07.88

30 Priority: 21.07.87 IT 6762887

43 Date of publication of application:
25.01.89 Bulletin 89/04

84 Designated Contracting States:
AT BE CH DE ES FR GB GR LI LU NL SE

71 Applicant: Bonetto, Claudio
 Via Exilles 51
 I-10146 Torino(IT)

Applicant: Bonetto, Luigi
 Corso Agnelli 102
 I-10137 Torino(IT)

Applicant: Loria, Ugo
 Via Fagnano 13
 I-10144 Torino(IT)

72 Inventor: Bonetto, Claudio
 Via Exilles 51
 I-10146 Torino(IT)

Inventor: Bonetto, Luigi
 Corso Agnelli 102
 I-10137 Torino(IT)

Inventor: Loria, Ugo
 Via Fagnano 13
 I-10144 Torino(IT)

74 Representative: Robba, Eugenio et al
 Studio "INTERPATENT" via Caboto 35
 I-10129 Turin(IT)

54 Safety device for car power windows.

57 On the edge of the glass receiving frame of the car there is provided a hollow (at 3) weather strip (1) within which two parallel conductors (5) extend spaced apart and are connected to an electric or electronic control unit (7) which is connected to the motor (9) of the power windows and to an outer control switch (11). In case of abnormal working conditions, a squashing of the cavity or channel (3) of the weather strip (1) causes a contact of the conductors (5) closing the circuit connected to a switch reversing the motion of the motor (9) in the control unit (7).

A temporary storage causes the window to continue the movement downwardly in spite of other commands sent to the device control unit.

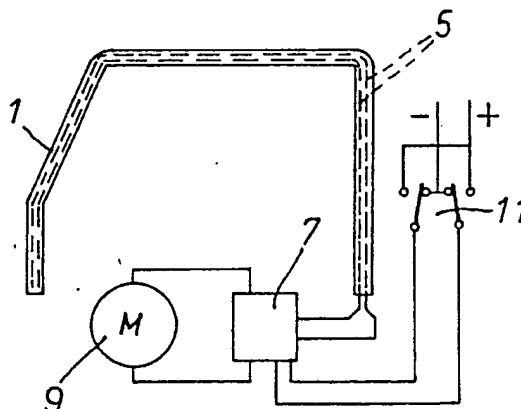


FIG. 1

"SAFETY DEVICE FOR CAR POWER WINDOWS"

The present invention concerns a safety device in a power window assembly for motor cars.

It is well known that the rapid spread of automatisms in the car industry has led to the installment of power windows in many type of motor cars.

It is also known that such automatic devices generally provide for an electric motor which is properly driven to actuate the power window assembly to raise and lower the car windows.

It is to be understood that such electric motors for power window assemblies are dimensioned considering a number of different factors besides the width and the weight of the windows, which can adversely affect the smooth window sliding: e.g. the wear conditions, the dirt, the wet or dry state of the windows, dried or new seals or guides, and so on.

The above leads to some oversize of the dedicated electric motor so that the power of such motor is not just that required to raise the car windows, but it is considerably larger.

Therefore, in case an obstacle interferes with the raising of a window, such as a hand or other, such obstacle will be forcibly pressed by the rising window before the thermal switch intervenes to stop the motor.

Some measures have been taken to overcome such inconvenience: reference is made to sensitive switches intervening as soon as the motor begins to detect a certain stress, which works according to the principle of the thermal switch, or friction devices which although without stopping the motor, make it slip thus halting the window driven by it.

Nevertheless such safety devices only stop the rising window, which is not enough in some instances (e.g. in case when a child's limb put out is accidentally trapped).

It is an object of the present invention to eliminate said shortcomings, which are typical of the known safety devices, by providing a safety device which not only stops the window motor, but additionally reverses its movement, thereby lowering the window until the end of the window travel.

Another object of the present invention is to provide a safety device intervening at a pressure level which is quite lower than the intervention pressure of the above mentioned devices, and which is therefore sensible to a light contact such as the one with a child's limb.

The squash preventing device according to the present invention substantially comprises a hollow rubber weather strip extending along the contour of the car glass receiving frame, within cavity or channel which two electrical conductors extend parallel

to each other and spaced apart when the channel is not squashed, and are connected to an electric or electronic unit reversing the motor rotation, connected with both the windows electric motor and the outer control switch.

The working of the device is the following. In case the hollow weather strip of the glass receiving frame is squashed due to an interposed obstacle such as a passenger's hand or the like, the two parallel conductors are brought in contact, thereby closing a circuit and actuating the reverse switch within the control unit, which acts on the windows motor to reverse the direction of rotation.

After the intervention, the car window will continue the downward movement until the end of allowed travel.

According to an embodiment, the safety device substantially comprises a threadlike member or tension wire extending within the hollow weather strip of the glass receiving frame, properly tensioned so that in case of strip compression or squashing, said wire is transversely moved, which causes the closure of a contact and therefore the actuation of the control unit reversing the windows motor.

According to another embodiment, the hollow weather strip of the glass receiving frame is filled with a fluid, such as air, in contact with a sensor connected in turn to the reversing control unit, the squashing of the strip causing a displacement of the sensor and therefore actuating the reversing switch of the control unit acting on the windows motor.

The control unit supervising the working of the device, substantially comprises:

- a sensor assembly adapted to detect an even slight obstacle interposed between the glass edge and the edge of the interior compartment;
- an adapter circuit to convert and adapt a pulse received from the above mentioned sensor;
- a temporary storage allowing for the device motor to continue driving the window downward until the end of the travel in spite of other commands received by said motor;
- a circuit controlling the rotation reversal of the power windows device.

The electric control unit proposed as an alternative to the electronic control unit for the device substantially comprises:

- a normally open sensor, adapted to detect an even slight obstacle interposed between the glass edge and the edge of the interior compartment; and
- a reversal arrangement connected through relays with the sensor and the motor.

Additional features and advantages will be evident from the following detailed description with reference to some preferred embodiments of the invention, together with the attached drawings in which:

- Fig. 1 schematically illustrates an embodiment of the invention in which two parallel electric conductors are provided for in the channel of the weather strip;

- Fig. 2 is a part section showing the weather strip with the channel, fitted to the glass receiving frame of a motor car;

- Fig. 3 shows a modification of Fig. 2;

- Fig. 4 schematically shows a modification of the embodiment of Fig. 1 in which a tension wire is provided extending along the strip channel;

Fig. 5 is a schematic part section illustrating the construction of the tension wire of Fig. 4;

Fig. 6 schematically illustrates another embodiment of the device in which the hollow weather strip of the glass receiving frame is filled with a fluid, such as air;

Fig. 7 is a part section along the weather strip of such embodiment;

- Fig. 8 shows another embodiment of the weather strip of Fig. 7;

- Fig. 9 shows the circuit of the electronic control unit; and

- Fig. 10 shows the circuit of the electric control unit for the device.

As clearly shown in the Figures, the device of the invention substantially comprises a weather strip 1 to be fitted within the glass receiving frame of the car, which is made of rubber, such as a long life rubber, provided with a cavity or channel 3 extending along the whole length of the strip, in which two electric conductors 5 are properly positioned, which are connected to a control unit 7 which in turn is connected both with the windows motor 9 and with an outer control or command switch 11.

Fig. 2 clearly shows the two spaced apart conductors 5, positioned within the channel 3 of the strip 1, as well as the upper edge of the window glass 13 which is going to close upwardly into the seat 15 provided in the glass receiving frame as an end of travel for the glass.

In Fig. 3 there is shown another embodiment of the weather strip with the channel housing the conductors applied outside.

In view of the substantial equivalence of the arrangements, the weather strip shown in Fig. 3 is marked with 1', the channel with 3', and the two conductors within said channel 3' with 5'.

Figs 4 and 5 schematically show another embodiment of the device, in which embodiment a tension wire 17 extends along the channel 3 of the weather strip 1, the wire being kept under tension

in the channel and with one of its ends connected with a spring 19, and with the other end connected with a contact 21 easily closed when the deflection of wire 17 due to a deformation of the channel 3 will reduce its length, even if slightly.

The remaining portion is substantially identical with the portion just described of the embodiment providing for two parallel conductors (Figs 1-3).

In Figs 7 and 8 there is schematically shown another embodiment of the invention, in which embodiment the channel 3 of the weather strip 1 is filled with a fluid, e.g. air.

In such embodiment the channel 3 has to be coupled with a chamber 23 housing a sensor 25 or contact member adapted to be displaced (closed) in respect of a rest position (open), by the slight pressure of the fluid displacement in such chamber due to the squashing of the channel 3 of weather strip 1.

For the remaining all is like what has already been described.

In the control unit 7, the displacement of such membrane sensor 25 will generate a pulse which after being properly adapted and stored, will drive the windows motor 9 downwardly until the end of travel.

Thanks to the transitory storage, such movement cannot be stopped, as in other known devices, by other commands sent from outside to the control unit or to the motor.

Fig. 9 shows the circuit of the electronic control unit supervising the working of the device.

Substantially it comprises a sensor 31 actuating a temporary storage by means of an adapter circuit 33, which storage in turn actuates the circuit 37 commanding the reversal of motor M.

Since the circuit is not particularly complicated, the same is not described in detail: it is only pointed out that the sensor 31 is a simple contact member, the adapter circuit 33 includes a transistor 33.1, a diode 33.2 and resistors 33.3. The temporary storage 35 comprises two transistors 35.1 and 35.2, an electrolytic capacitor 35.3, two diodes 35.4 and 35.5, and properly connected resistors 35.6.

The circuit 37 commanding the reversal of motor M comprises push button switches 37.1, remotely controlled switches 37.2, and two relays 37.3 and 37.4, properly filtered by a diode 37.5.

The electric control unit is provided with a slightly different electric circuit which is shown in Fig. 10.

It can be seen that such circuit substantially comprises a sensor 41, a reversal arrangement 43 for the direction of rotation of motor M, and control push buttons 45.

More particularly, the circuit 43 reversing the direction of rotation of motor M comprises two

switches 43.1 controlled by relays 43.2 connected with another switch 43.3 actuated by a relay 43.4, as well as feeding and safety diodes 43.5 and 43.6.

Claims

1. A safety device for car power windows characterized in that it substantially comprises a hollow (at 3) rubber weather strip (1) extending along the contour of the car glass receiving frame, within which cavity or channel (3) two electric conductors (5) extend parallel to each other and spaced apart when the channel is not squashed, and are connected to an electric or electronic unit (7) reversing the motor rotation, connected with both the windows electric motor (9) and the outer control switch (11).

2. A safety device for car power windows as claimed in claim 1, characterized in that it substantially comprises a threadlike member (17) or tension wire extending within (3) the hollow weather strip (1) of the glass receiving frame, properly tensioned so that in case of strip compression or squashing, said wire (17) is transversely moved, which causes the closure of a contact (21) and therefore the actuation of the control unit reversing the windows motor (9).

3. A safety device for car power windows as claimed in claim 1 or 2, characterized in that the hollow (at 3) weather strip (1) of the glass receiving frame is filled with a fluid, such as air, in contact with a sensor (25) connected in turn to the reversing control unit (7), the squashing of the strip (3) causing a displacement of the sensor (25) and therefore actuating the reversing switch of the control unit (7) acting on the windows motor (9).

4. A safety device for car power windows according to the preceding claims characterized in that the control unit supervising the working of the device, substantially comprises:

- a sensor assembly (31) adapted to detect an even slight obstacle interposed between the glass edge and the edge of the interior compartment;

- an adapter circuit (33) to convert and adapt a pulse received from the above mentioned sensor (31);

- a temporary storage (35) allowing for the device motor (M) to continue driving the window downward until the end of the travel in spite of other commands received by said motor (M);

- a circuit (37) controlling the rotation reversal of the motor (M) of the power windows device.

5. A safety device for car power windows according to the preceding claims, characterized in that the electric control unit proposed as an alternative to the electronic control unit for the device substantially comprises:

- a normally open sensor (41), adapted to detect an even slight obstacle interposed between the glass edge and the edge of the interior compartment; and

- a reversal arrangement (43) connected through relays with the sensor (41) and the motor (M).

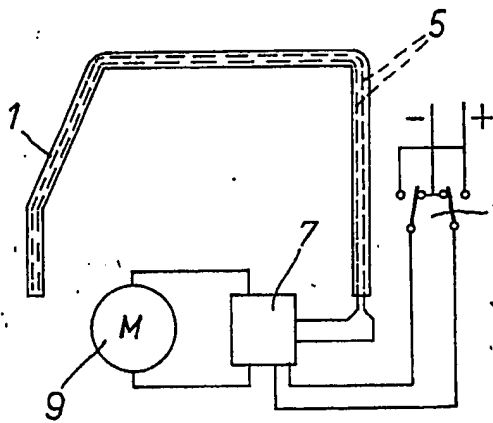


FIG. 1

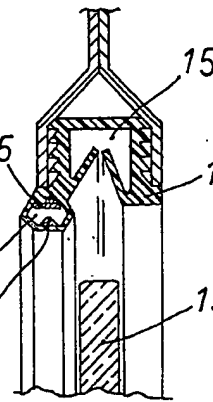


FIG. 2

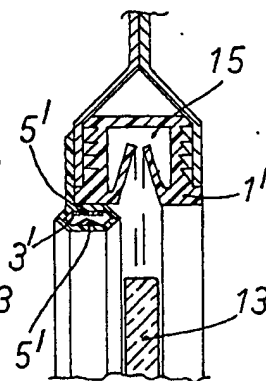


FIG. 3

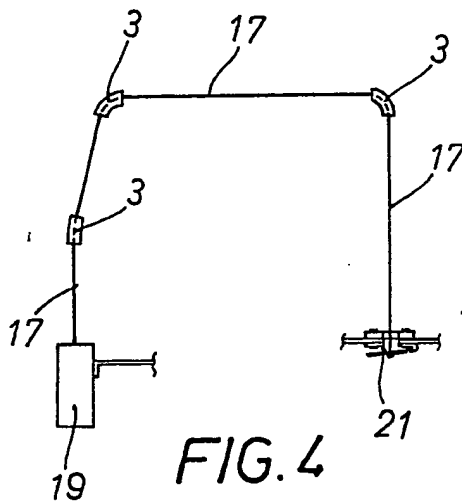


FIG. 4

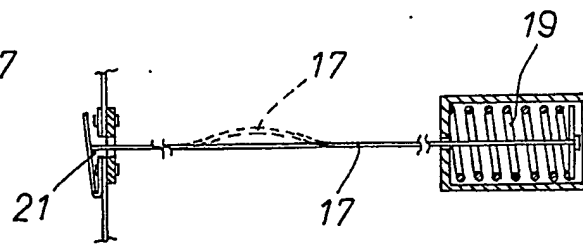


FIG. 5

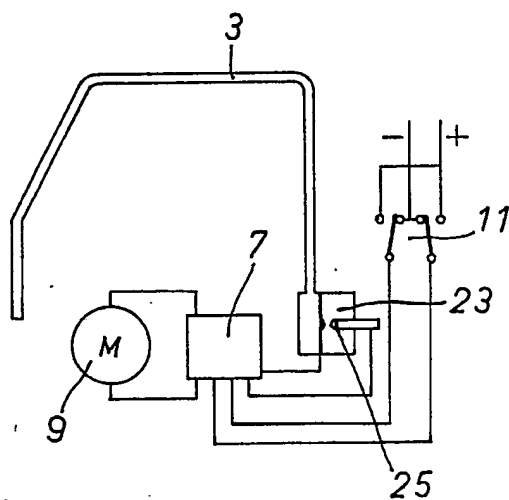


FIG. 6

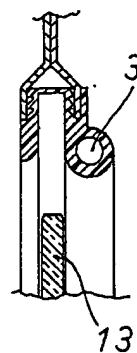


FIG. 7

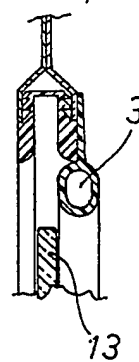


FIG. 8

